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(54) Title: DOPED PARTICULATE SILICON PARTICLE SIZE SELECTION

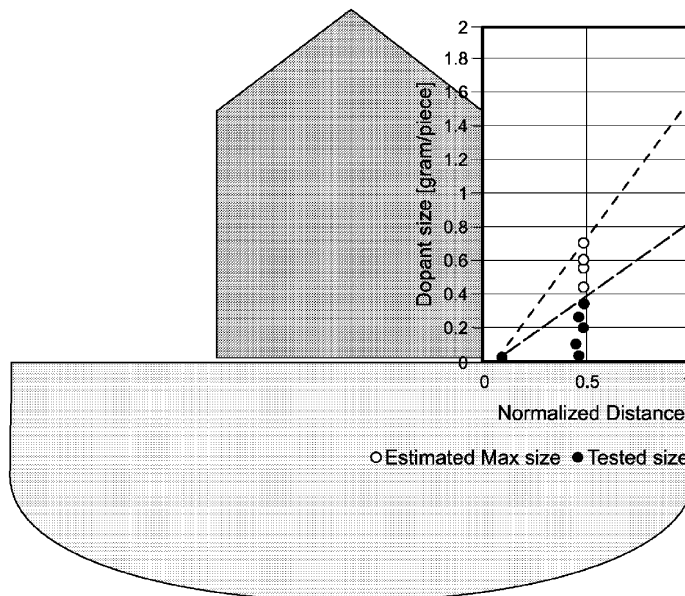


FIG. 9

(57) Abstract: Methods for doping a silicon melt with doped particulate silicon are disclosed. Maximum particle size of the doped particulate silicon may be controlled based on the impact region of the doped particulate silicon on the silicon melt.

[Continued on next page]

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